NPN Silicon Power Transistors High Voltage Planar

The MJW18020 planar High Voltage Power Transistor is specifically Designed for motor control applications, high power supplies and UPS's for which the high reproducibility of DC and Switching parameters minimizes the dead time in bridge configurations.

Features

- High and Excellent Gain Linearity
- Fast and Very Tight Switching Times Parameters tsi and tfi
- Very Stable Leakage Current due to the Planar Structure
- High Reliability
- Pb-Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Sustaining Voltage	V _{CEO}	450	Vdc
Collector-Base Breakdown Voltage	V _{CES}	1000	Vdc
Collector-Base Voltage	V _{CBO}	1000	Vdc
Emitter-Base Voltage	V _{EBO}	9.0	Vdc
Collector Current - Continuous - Peak (Note 1)	I _C	30 45	Adc
Base Current - Continuous - Peak (Note 1)	Ι _Β	6.0 10	Adc
Total Power Dissipation @ T _C = 25°C Derate Above 25°C	P _D	250 2.0	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	TL	275	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

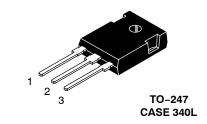
1. Pulse Test: Pulse Width = 5 μ s, Duty Cycle \leq 10%.



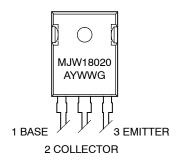
ON Semiconductor®

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30 AMPERES 1000 VOLTS BV_{CES} 450 VOLTS BV_{CEO.} 250 WATTS



MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJW18020	TO-247	30 Units/Rail
MJW18020G	TO-247 (Pb-Free)	30 Units/Rail

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic Symbol Min Typ Max Unit						
	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS			450	1	1	\
Collector-Emitter Sustaining Voltage ($I_C = 100 \text{ mAdc}, I_B = 0$)		$V_{CEO(sus)}$	450	_	_	Vdc
Collector Cutoff Current $(V_{CE} = Rated V_{CEO}, I_B = 0)$		I _{CEO}	_	_	100	μAdc
Collector Cutoff Current (V _{CE} = Rated V _C (T _C = 125°C)	_{ES} , V _{EB} = 0)	I _{CES}	-	-	100 500	μAdc
Emitter Cutoff Current (V _{CE} = 9 Vdc, I _C = 0)	I _{EBO}	-	_	100	μAdc	
ON CHARACTERISTICS						
DC Current Gain (I _C = 3 Adc, V _{CE} = 5		h _{FE}	14		34	
$(I_C = 10 \text{ Adc } V_{CE} = 2)$	(T _C = 125°C)		- 8	30 16	_	
·	(T _C = 125°C)		5	14	_	
$(I_C = 20 \text{ Adc } V_{CE} = 2)$! Vdc) (T _C = 125°C)		5.5 4	9	_ _	
(I_C = 10 mAdc V_{CE} =			14	25	_	
Base–Emitter Saturation Voltage ($I_C = 10$ ($I_C = 20$) Adc, I _B = 2 Adc)) Adc, I _B = 4 Adc)	V _{BE(sat)}	-	0.97 1.15	1.25 1.5	Vdc
Collector-Emitter Saturation Voltage		V _{CE(sat)}				Vdc
$(I_C = 10 \text{ Adc}, I_B = 2 \text{ Adc})$	(T. 10500)	OL(Sai)	_	0.2	0.6	
(I _C = 20 Adc, I _B = 4 Adc)	$(T_C = 125^{\circ}C)$		_	0.3 0.5	1.5	
, , ,	$(T_C = 125^{\circ}C)$		-	0.9	2.0	
DYNAMIC CHARACTERISTICS						
Current Gain Bandwidth Product ($I_C = 1$ Adc, $V_{CE} = 10$ Vdc, $f_{test} = 1$ MHz)		f _T	-	13	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz)		C _{ob}	-	300	500	pF
Input Capacitance (V _{EB} = 8.0)		C _{ib}	-	7000	9000	pF
SWITCHING CHARACTERISTICS: Resi	stive Load (D.C. = 10%, Pulse Width	= 70 μs)	1		I	
Turn-On Time	$(I_C = 10 \text{ Adc}, I_{B1} = I_{B2} = 2 \text{ Adc}, \\ Vcc = 125 \text{ V})$	t _{On}	-	540	750	ns
Storage Time		t _s	_	4.75	6	μs
Fall Time		t _f	_	380	500	ns
Turn-Off Time		t _{Off}	_	5.2	6.5	μs
Turn-On Time	$(I_C = 20 \text{ Adc}, I_{B1} = I_{B2} = 4 \text{ Adc},$	t _{On}	-	965	1200	ns
Storage Time	Vcc = 125 V)	t _s	_	2.9	3.5	μs
Fall Time		t _f	-	350	500	ns
Turn-Off Time		t _{Off}	-	3.25	4	μs
SWITCHING CHARACTERISTICS: Indu	ctive Load (V _{clamp} = 300 V , Vcc = 15	V, L = 200 μH)	_			
Fall Time	$(I_C = 10 \text{ Adc}, I_{B1} = I_{B2} = 2 \text{ Adc})$	t _{fi}	-	142	250	ns
Storage Time		t _{si}	-	4.75	6	μs
Crossover Time		t _C	-	320	500	ns
Fall Time $(I_C = 20 \text{ Adc}, I_{B1} = I_{B2} = 4 \text{ Adc})$		tfi	-	350	500	ns
Fall Time				<u> </u>		
Fall Time Storage Time		t _{si}	-	3.0	3.5	μs

TYPICAL CHARACTERISTICS

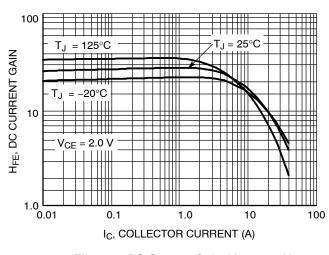


Figure 1. DC Current Gain, V_{CE} = 2.0 V

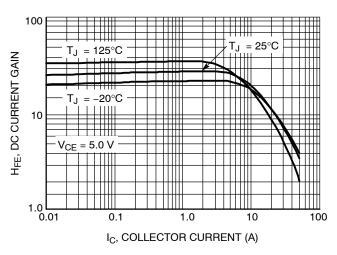


Figure 2. DC Current Gain, V_{CE} = 5.0 V

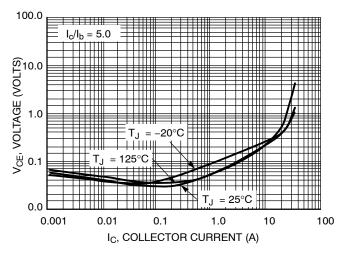


Figure 3. Typical Collector–Emitter Saturation Voltage, $I_C/I_B = 5.0$

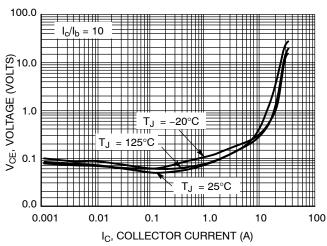


Figure 4. Typical Collector–Emitter Saturation Voltage, $I_C/I_B = 10$

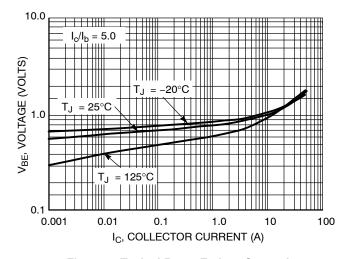


Figure 5. Typical Base–Emitter Saturation Voltage, $I_C/I_B = 5.0$

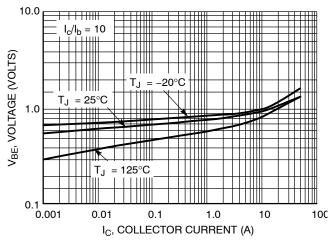


Figure 6. Typical Base–Emitter Saturation Voltage, I_C/I_B = 10

TYPICAL CHARACTERISTICS

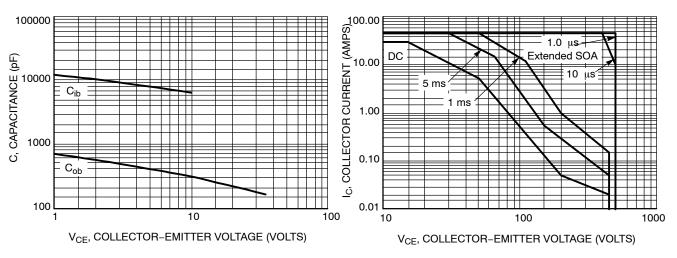


Figure 7. Typical Capacitance

Figure 8. Forward Bias Safe Operating Area

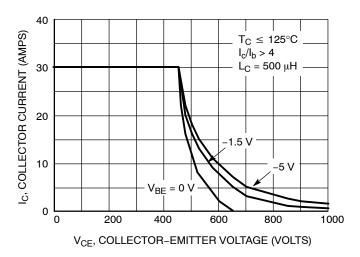
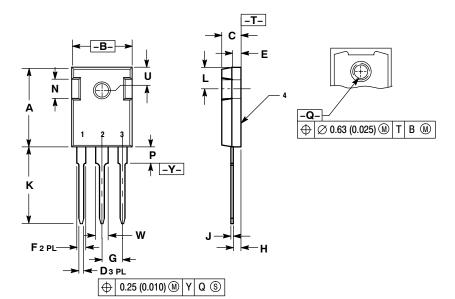


Figure 9. Reverse Bias Safe Operating Area

PACKAGE DIMENSIONS

TO-247 CASE 340L-02 **ISSUE E**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	20.32	21.08	0.800	8.30	
В	15.75	16.26	0.620	0.640	
С	4.70	5.30	0.185	0.209	
D	1.00	1.40	0.040	0.055	
Е	1.90	2.60	0.075	0.102	
F	1.65	2.13	0.065	0.084	
G	5.45 BSC		0.215 BSC		
Н	1.50	2.49	0.059	0.098	
J	0.40	0.80	0.016	0.031	
K	19.81	20.83	0.780	0.820	
L	5.40	6.20	0.212	0.244	
N	4.32	5.49	0.170	0.216	
Р		4.50		0.177	
Q	3.55	3.65	0.140	0.144	
U	6.15	6.15 BSC 0.242 BSC		BSC	
W	2.87	3.12	0.113	0.123	

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